

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	IS&P	L1	4761	(250/306,307,310,311,492.3,492.2,492.22).CCLS.	USPAT; US-PGP UB	2002/08/22 16:49
2	BRS	L2	7216	(silicon adj on adj insulator) or SOI	USPAT; US-PGP UB	2002/08/22 17:18
3	BRS	L3	44	L1 and L2	USPAT; US-PGP UB	2002/08/22 16:51
4	BRS	L4	0	L3 and (inspection with (electron or SEM))	USPAT; US-PGP UB	2002/08/22 17:19
5	BRS	L6	4	L5 and (substrate near2 remov\$3)	USPAT; US-PGP UB	2002/08/22 17:02
6	BRS	L5	14	L3 and ((electron adj beam) or SEM)	USPAT; US-PGP UB	2002/08/22 17:00
7	BRS	L7	1	L5 and inspect\$4	USPAT; US-PGP UB	2002/08/22 17:00
8	BRS	L8	227	L1 and (inspection with (electron or SEM))	USPAT; US-PGP UB	2002/08/22 17:01
9	BRS	L9	8	L8 and (substrate near2 remov\$3)	USPAT; US-PGP UB	2002/08/22 17:22
10	BRS	L10	46	L8 and (imag\$4 near3 defect)	USPAT; US-PGP UB	2002/08/22 17:23
11	BRS	L11	6	L10 and (bright near4 dark)	USPAT; US-PGP UB	2002/08/22 17:18
12	BFS	L12	6238	(silicon adj on adj insulator) or SOI	EPO; JPO; DEFWEN T; IBM_TD B	2002/08/22 17:19

	Comments	Error Definition	Errors
1			0
2			0
3			0
4			0
5			0
6			0
7			0
8			0
9			0
10			0
11			0
12			0

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	1	L12 and (inspection with (electron or SEM))	EPO; JPO; DERWEN T; IBM_TD B	2002/08/22 17:21
14	BRS	L14	26	(semiconductor near2 die)and (inspection with (electron or SEM))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/08/22 17:22
15	BRS	L15	0	L14 and (substrate near2 remov\$3)	USPAT; US-PGP UB	2002/08/22 17:23
16	BRS	L16	0	L14 and (substrate near2 remov\$3)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/08/22 17:23
17	BRS	L18	0	L14 and (imag\$4 near3 defect)	EPO; JPO; DERWEN T; IBM_TD B	2002/08/22 17:24
18	BRS	L17	8	L14 and (imag\$4 near3 defect)	USPAT; US-PGP UB	2002/08/22 17:24

	Comments	Error Definition	Errors
13			0
14			0
15			0
16			0
17			0
18			0